

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ\text{C}$
30V	18m Ω @ $V_{GS} = 10\text{V}$	9.0A
	30m Ω @ $V_{GS} = 4.5\text{V}$	7.0A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

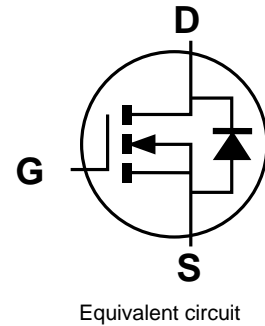
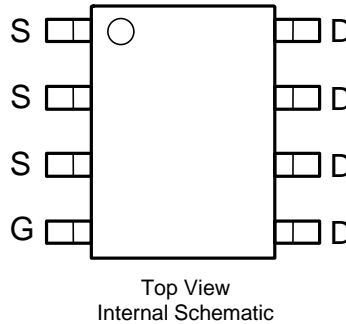
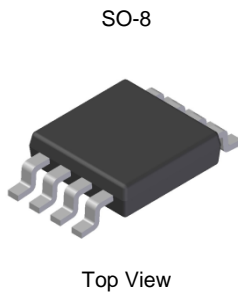
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (Approximate)

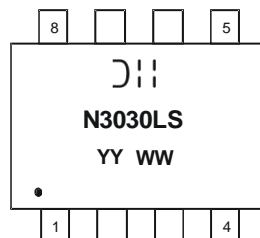
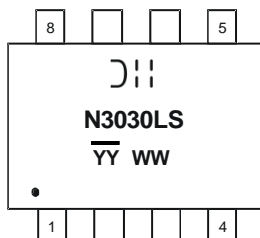


Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3030LSS-13	SO-8	2500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, see <http://www.diodes.com/products/packages.html>.

Marking Information



- ⌋⌋ = Manufacturer's Marking
- N3030LS = Product Type Marking Code
- YYWW = Date Code Marking
- YY or YY = Year (ex: 13 = 2013)
- WW = Week (01 - 53)
- YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
- YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±25	V
Drain Current (Note 6)	I _D	T _A = +25°C	9.0
		T _A = +70°C	6.75
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	40	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	1.7	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	73	°C/W
Total Power Dissipation (Note 6)	P _D	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	50	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
		—	—	±1	µA	V _{GS} = ±25V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	1	—	2.1	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	15.7	18	mΩ	V _{GS} = 10V, I _D = 9A
		—	26.4	30	mΩ	V _{GS} = 4.5V, I _D = 7A
Forward Transconductance	g _{fs}	—	5.8	—	S	V _{DS} = 10V, I _D = 9A
Diode Forward Voltage	V _{SD}	0.5	0.7	1.2	V	V _{GS} = 0V, I _S = 2.1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	741	—	pF	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	124	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	95	—	pF	
Gate Resistance	R _G	0.30	0.88	2.5	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
SWITCHING CHARACTERISTICS (Note 8)						
Total Gate Charge	Q _g	—	7.6	12	nC	V _{DS} = 15V, V _{GS} = 4.5V, I _D = 9A
		—	16.7	25		
Gate-Source Charge	Q _{gs}	—	1.9	—	ns	V _{DS} = 15V, V _{GS} = 10V, I _D = 9A
Gate-Drain Charge	Q _{gd}	—	5.2	—		
Turn-On Delay Time	t _{d(on)}	—	4.0	—		
Rise Time	t _r	—	4.4	—	ns	V _{GS} = 10V, V _{DS} = 15V, R _L = 15Ω, R _G = 6Ω
Turn-Off Delay Time	t _{d(off)}	—	23.0	—		
Fall Time	t _f	—	9.4	—		

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

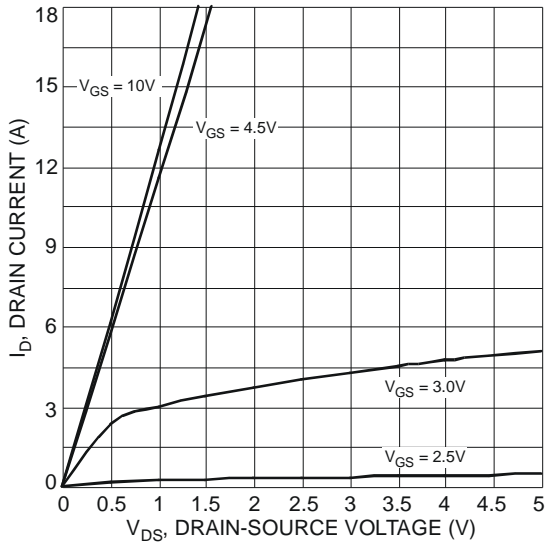


Fig. 1 Typical Output Characteristic

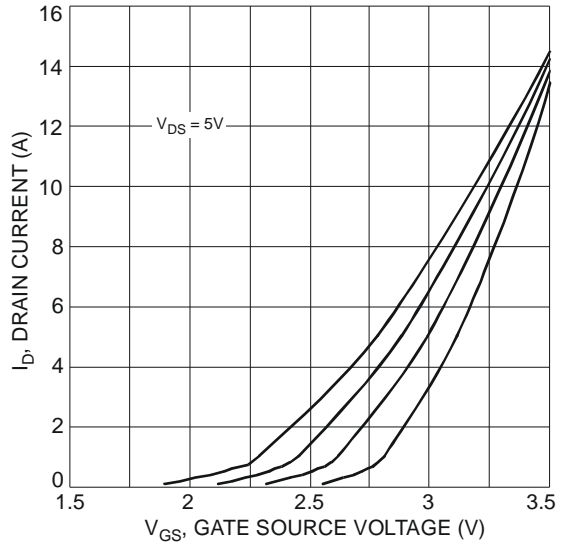


Fig. 2 Typical Transfer Characteristics

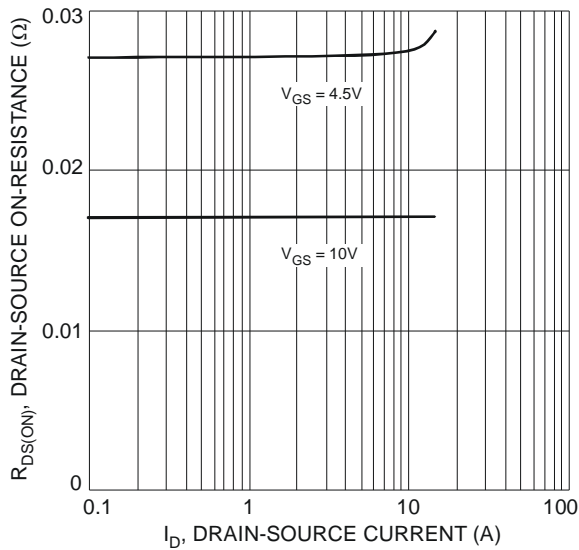


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

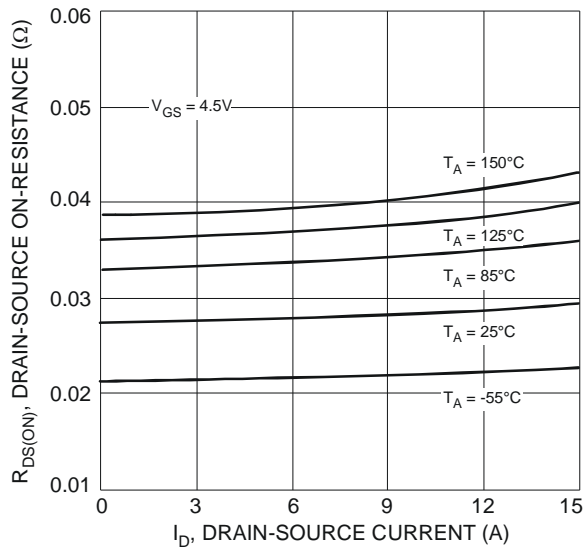


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

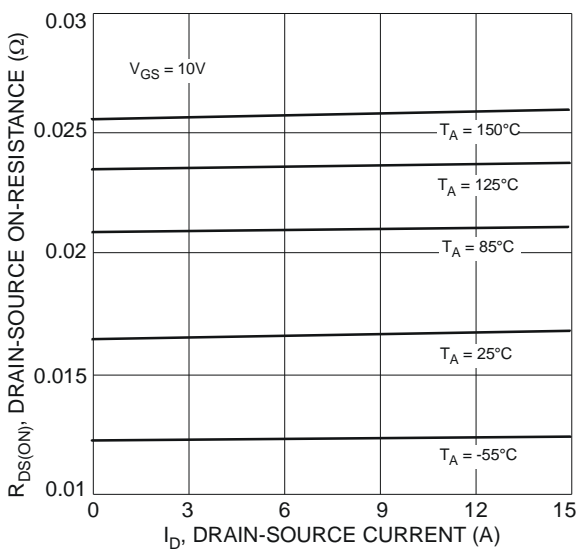


Fig. 5 Typical On-Resistance vs. Drain Current and Temperature

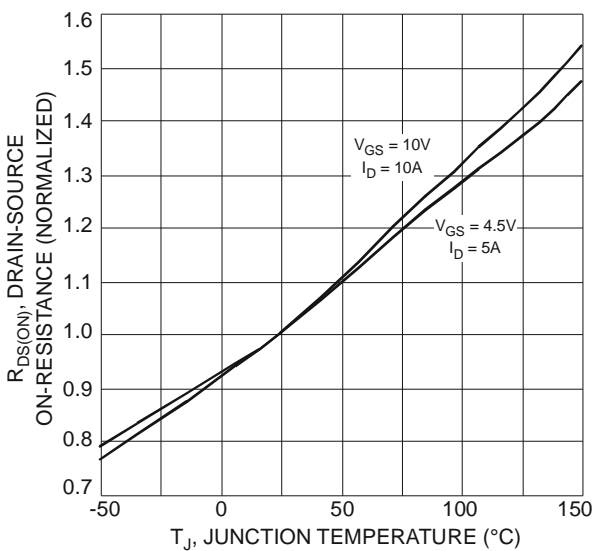


Fig. 6 On-Resistance Variation with Temperature

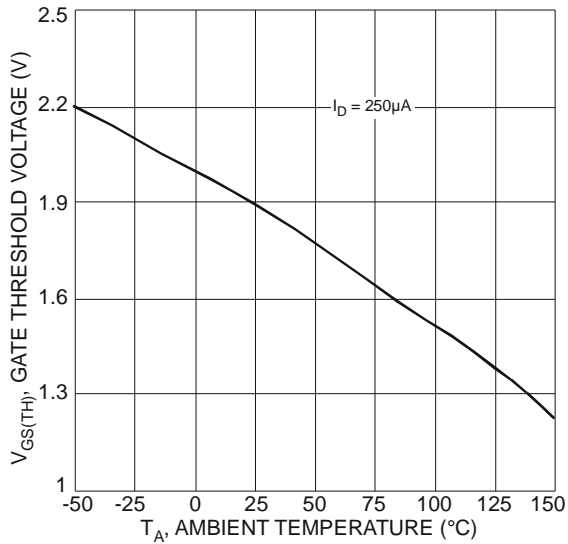


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

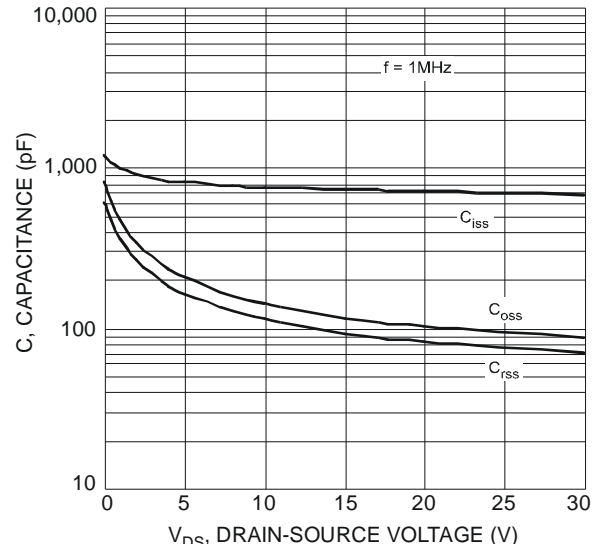


Fig. 8 Total Capacitance

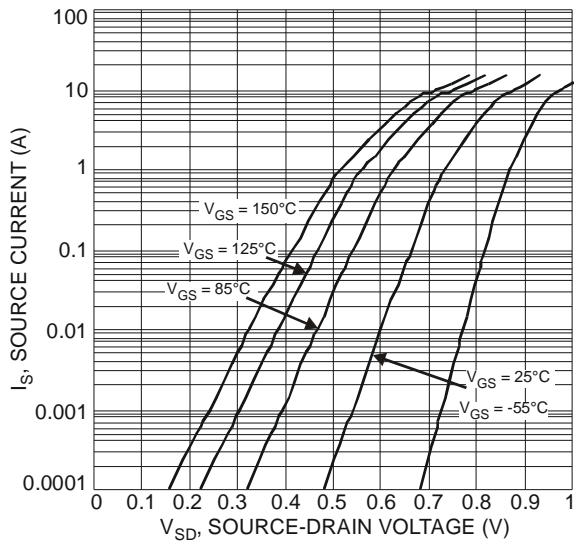


Fig. 9 Diode Forward Voltage vs. Current

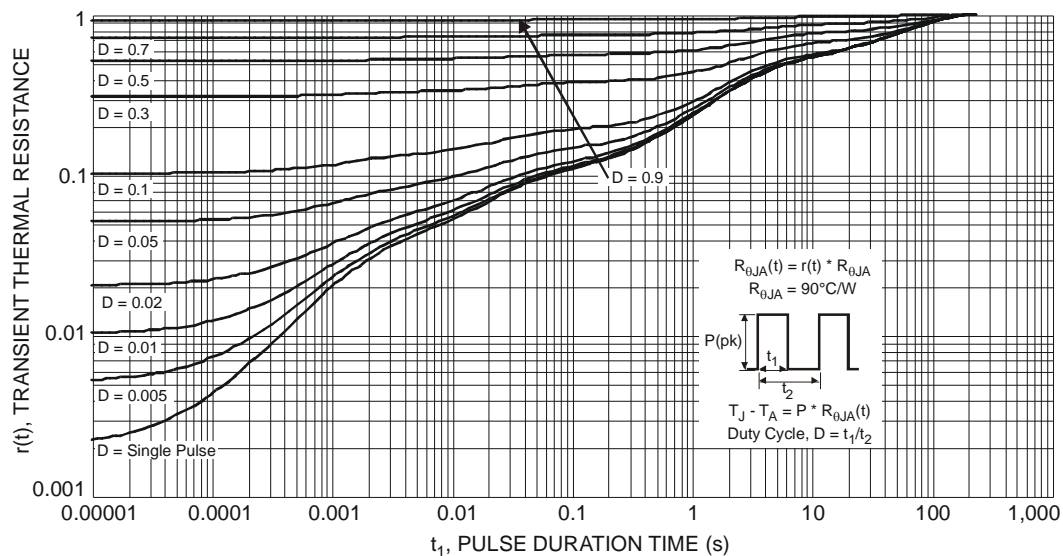
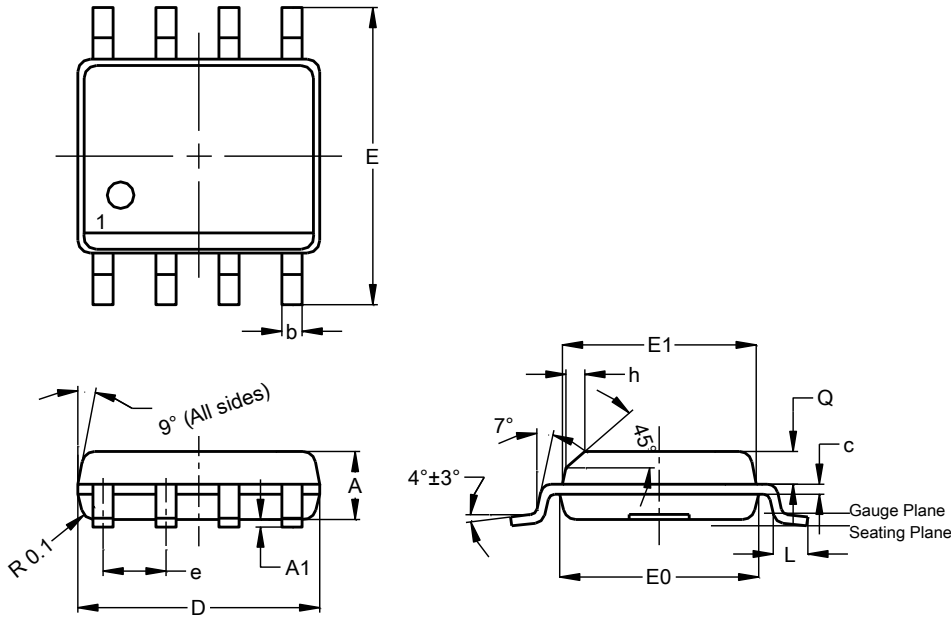


Fig. 10 Transient Thermal Response

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8

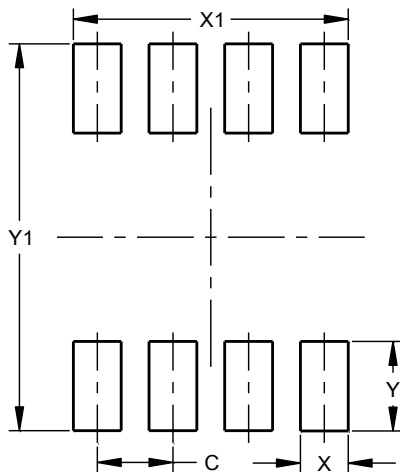


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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